

Attorney Docket No. 59521 (48229)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT: Hiroyuki Shimada

EXAMINER: Chen Kin Chan

U.S.S.N.: 10/678,994

GROUP ART UNIT: 1765

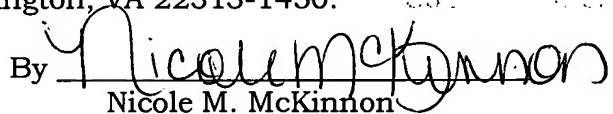
FILED: October 3, 2003

CONFIRMATION NO.: 8918

FOR: METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE
INCLUDING ETCHING A CONDUCTIVE LAYER BY USING A GAS
INCLUDING SiCl₄ and NF₃

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By 
Nicole M. McKinnon

Mail Stop AMENDMENT
Commissioner for Patents
P.O. Box 1450
Arlington, VA 22313-1450

Sir:

AMENDMENT UNDER 37 C.F.R. § 1.111

In response to the Office Action dated June 20, 2005, Applicant submits the following amendment.

Amendment Under 37 C.F.R. § 1.111

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IN THE TITLE:

Please change the title to the following title:

METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE INCLUDING
ETCHING A CONDUCTIVE LAYER BY USING A GAS INCLUDING SiCl₄ and
NF₃